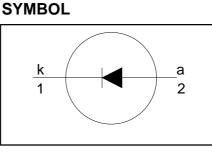
Philips Semiconductors

Rectifier diodes ultrafast

FEATURES

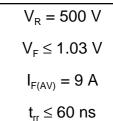
- · Low forward volt drop
- Fast switching
- Soft recovery characteristic
- High thermal cycling performance
- Low thermal resistance



Product specification

BYV29B-500

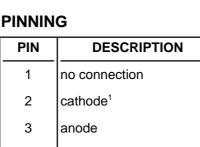
QUICK REFERENCE DATA



GENERAL DESCRIPTION

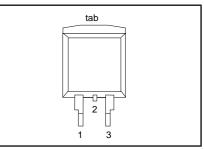
Ultra-fast, epitaxial rectifier diodes intended for use as output rectifiers in high frequency switched mode power supplies.

The BYV29B-500 is supplied in the SOT404 surface mounting package.



tab cathode

SOT404 (D²-PAK)



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	Peak repetitive reverse voltage		-	500	V
V _{RWM}	Crest working reverse voltage		-	500	
V _R	Continuous reverse voltage		-	500	V
I _{F(AV)}	Average forward current ²	square wave; $\delta = 0.5$; T _{mb} ≤ 123 °C	-	9	A
I I _{FRM}	Repetitive peak forward current	t = 25 μs; δ = 0.5; T _{mb} ≤ 123 °C	-	18	A
I _{FSM}	Non-repetitive peak forward	t = 10 ms	-	100	A
	current.	t = 8.3 ms sinusoidal; with reapplied V _{RRM(max)}	-	110	A
T _{stg}	Storage temperature		-40	150	°C
Τ _j	Operating junction temperature		-	150	°C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-mb}	Thermal resistance junction to		-	-	2.5	K/W
R _{th j-a}	mounting base Thermal resistance junction to ambient	minimum footprint, FR4 board.	-	50	-	K/W

¹ it is not possible to make a connection to pin 2 of the SOT404 package

² Neglecting switching and reverse current losses.

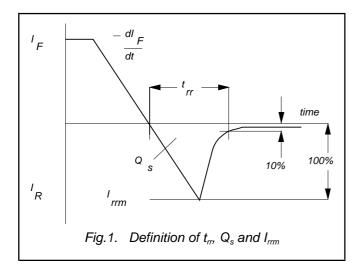
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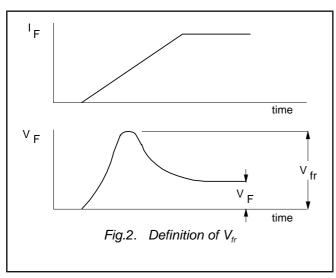
BYV29B-500

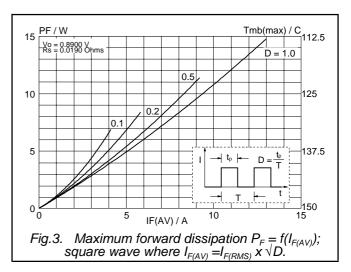
ELECTRICAL CHARACTERISTICS

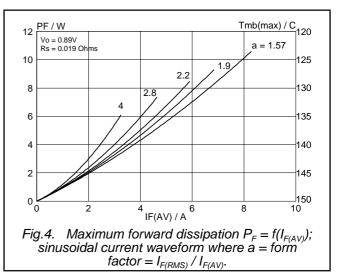
 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	Forward voltage	I _F = 8 A; T _i = 150°C	-	0.90	1.03	V
		$I_F = 8 A$	-	1.05	1.25	V
		$I_{\rm F} = 20 {\rm A}$	-	1.20	1.40	V
I _R	Reverse current	$V_{R} = V_{RRM}$	-	2.0	50	μA
		$V_R = V_{RRM}$; T _j = 100 °C I _F = 2 Å to V _R ≥ 30 V;	-	0.1	0.35	mΑ
Q_s	Reverse recovery charge	$I_F = 2 \text{ A to } V_R \ge 30 \text{ V};$	-	40	60	nC
-		$dI_{F}/dt = 20 A/\mu s$				
t _{rr}	Reverse recovery time	$I_F = 1 \text{ A to } V_R \ge 30 \text{ V};$	-	50	60	ns
	-	$dI_F/dt = 100 A/\mu s$				
l _{rrm}	Peak reverse recovery current	$I_{\rm F} = 10 \text{ A to } V_{\rm R} \ge 30 \text{ V};$	-	4.0	5.5	Α
		$dI_{\rm F}/dt = 50 \text{ A}/\mu \text{s}; T_{\rm i} = 100^{\circ}\text{C}$				
V _{fr}	Forward recovery voltage	$I_{F} = 10 \text{ A}; \text{ d}I_{F}/\text{d}t = 10 \text{ A}/\mu\text{s}$	-	2.5	-	V



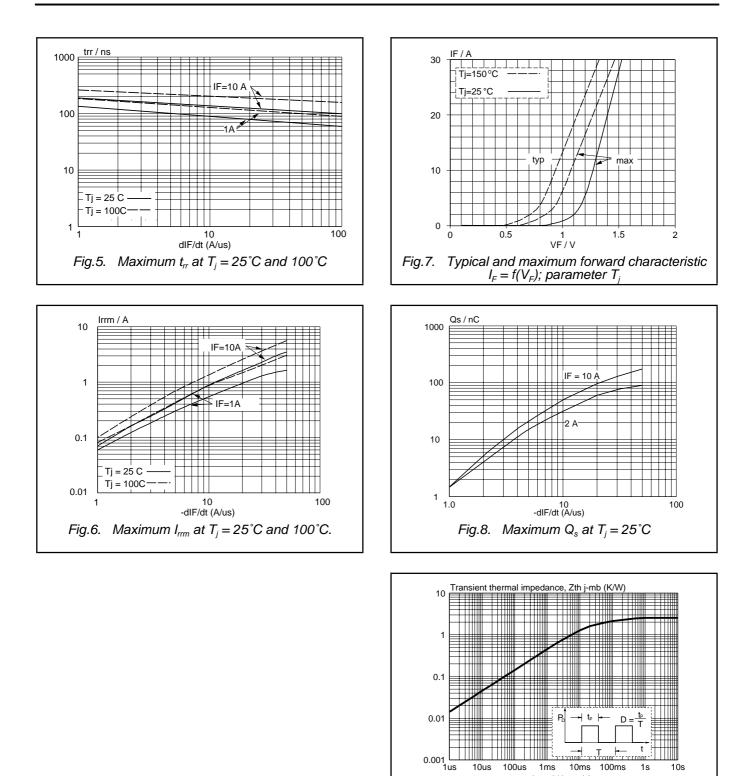






BYV29B-500

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10us

100us

1ms

pulse width, tp (s) Fig.9. Transient thermal impedance $Z_{th i-mb} = f(t_p)$

10ms

100ms

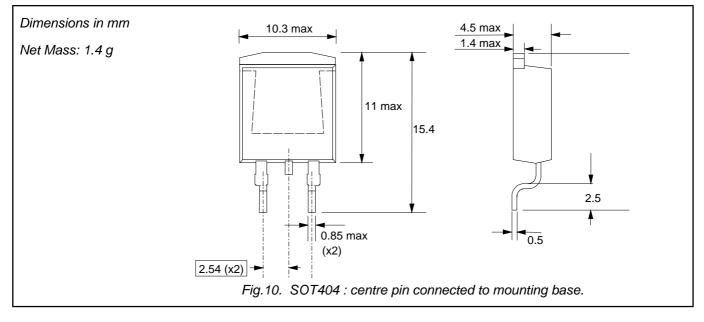
1s

10s

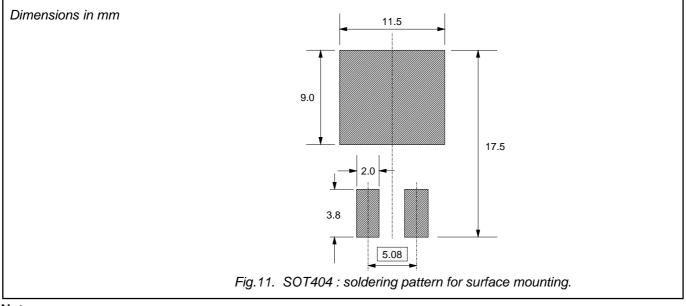
Rectifier diodes ultrafast

BYV29B-500

MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes

1. Epoxy meets UL94 V0 at 1/8".

Rectifier diodes ultrafast

BYV29B-500

DEFINITIONS

DATA SHEET STATUS				
DATA SHEET PRODUCT STATUS ³ STATUS ⁴		DEFINITIONS		
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice		
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in ordere to improve the design and supply the best possible product		
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A		

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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³ Please consult the most recently issued datasheet before initiating or completing a design.

⁴ The product status of the device(s) described in this datasheet may have changed since this datasheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.